Active
- L1: (2646) vertical near3 (MOS MOSFET)
- L2: (150) 1 with (pitch or thickness)
- L3: (66) 2 with (drain or source or channel)
- L4: (501) 1 with (opening trench$2 groove recess$2 trough)
- L8: (177) 438/192
- L9: (8) 8 and 4
- L10: (175) 438/206
- L11: (20) 10 and 4
- L12: (16) 11 not 9
- L13: (102) 438/173
- L14: (5) 13 and 4
- L15: (350) 438/212
- L16: (33) 15 and 4
- L17: (22) 16 not 11
- L18: (257) 438/137,138.ccls.
- L19: (15) 18 and 4
- L20: (15) 19 not 12
- L21: (14) 20 not 17
- L22: (12) 21 not 3
- L23: (334) 438/156
- L24: (12) 23 and 4
- L25: (11) 24 not 22
- L26: (102) 438/173
- L27: (5) 26 and 4
- L29: (177) 438/192
- L30: (8) 29 and 4
- L32: (785) 438/192,206,209,212,268.ccls.
- L33: (55) 32 and 4
- L34: (41) 33 not 17
- L35: (37) 34 not 22
- L36: (5643) 438/396
- L37: (4) 36 and 4
- L40: (0) 39 and 4
- L41: (3745) 438/253
- L42: (6) 41 and 4
- L43: (699) 438/244
- L44: (10) 43 and 4
- L45: (3745) 438/253
- L46: (6) 45 and 4
- L47: (1658) vertical near3 MOS
- L48: (475) (vertical near3 MOS).ab.
- L49: (176) 48 and (drain or source or channel)
- L50: (4) ("4740826" | "5443992" | "5920088" | "6153905").PN.
- L51: (569) 438/269,270.ccls.
- L53: (98) 52 and 4
- L55: (82) 53 not 35
- L56: (69) 55 not 17

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DBs: USPAT;US-PGPUB;EPO

Default operator: OR

78 and 79

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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval	C	Inventor	B	C	P				Im
1			US 20040061178	20040401	14	Finfet having improved carri	257/350	257/328;			Lin, Ming-Ren et al.							

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L46:  (6)  45 and 4
L47:  (1658)  vertical near3 MOS
L48:  (475)  (vertical near3 MOS).ab.
L49:  (176)  48 and (drain or source or channel)
L50:  (4)  ("4740826" | "5443992" | "5920088" | "6153905").PN.
L51:  (569)  438/269,270.ccls.
L53:  (98)  52 and 4
L55:  (82)  53 not 35
L56:  (69)  55 not 17
L57:  (55)  56 not 49
L58:  (53)  57 not 12
L59:  (2198)  257/192,330,331.ccls.
L60:  (123)  59 and 4
L61:  (114)  60 not 58
L62:  (111)  61 not 12
L63:  (102)  62 not 17
L64:  (87)  63 not 49
L65:  (83)  64 not 35
L66:  (4)  ("4740826" | "5443992" | "5920088" | "6153905").PN.
L67:  (3)  6300198.URPN.
L68:  (4)  ("5365097" | "5382816" | "5872037" | "6300198").PN.
L69:  (2)  (("6638823") or ("6184090")).PN.
L70:  (4)  ("5365097" | "5382816" | "5872037" | "6300198").PN.
L71:  (1)  "5891770".PN.
L72:  (2)  6184090.URPN.
L73:  (3)  ("6184090" | "6271081" | "6418050").PN.
L74:  (1)  ("6207977").PN.
L75:  (1)  ("4740826").PN.
L76:  (4)  ("3518509" | "4462040" | "4554570" | "4566025").PN.
L77:  (7)  ("3412297" | "3564358" | "3600651" | "4101350" | "4375717" | "4472729" | "4479297").PN.
L78:  (2646)  vertical near3 (MOS MOSFET)
L79:  (1788)  438/149
L80:  (20)  78 and 79
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Failed
Saved

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(3)  (("5208172") or ("5545586") or ("5376562")).PN.
(4)  ("4663831" | "4764801" | "4860077" | "4902641").PN.
(24)  5208172.URPN.
(2646)  vertical near3 (MOS MOSFET)
(1736098)  opening trench$2 groove recess$2 trough
(204276)  (insulat$3 dielectric) near (film layer)
(1463)  (vertical near3 (MOS MOSFET)) and (opening trench$2 groove recess$2 trough) and ((insulat...
(560)  ((vertical near3 (MOS MOSFET)) and (opening trench$2 groove recess$2 trough) and ((insulat...
(4789)  (source and drain) with (sequence stack$2)
(29)  (((vertical near3 (MOS MOSFET)) and (opening trench$2 groove recess$2 trough) and ((insulat...
(9)  ("4236166" | "4550489" | "4740826" | "4788158" | "5398200" | "5414655" | "5451800" | "549701...
(22)  ("4364074" | "4653025" | "4740826" | "4794561" | "4821235" | "4890144" | "4920397" | "49299...
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1		US 20040061178	20040401	14	Finfet having improved carri	257/350	257/328;		Lin, Ming-Ren et al.	P				US

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